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PATENT

Attorney Docket No.: SAM-0298

P/C
12/3/02
SPIN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Jae-Hak Kim, et al. ✓
Serial No.: 09/994,508 ✓
Filing Date: November 27, 2001 ✓
Title: METHOD OF FABRICATING SEMICONDUCTOR DEVICES HAVING LOW
DIELECTRIC INTERLAYER INSULATION LAYER

Examiner: Rao, S.
Group Art Unit: 2814

CERTIFICATE OF MAILING UNDER 37 C.F.R. § 1.8

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12-6-02

Date

Amy Green

BOX AF

Assistant Commissioner for Patents
Washington, D.C. 20231

enter
marshu/4/03AMENDMENT AFTER FINAL REJECTION

Sir:

This is in response to the final Office Action mailed on September 26, 2002. It is requested that the following amendments be entered and that the following remarks be considered.

Please amend the application as follows:

In the Claims

1. (Twice Amended) A method of fabricating a semiconductor device having a low dielectric interlayer insulation layer, the method comprising:
- forming a silicon oxycarbide layer as the low dielectric interlayer insulation layer on a substrate;
 - treating the formed silicon oxycarbide layer with plasma; and
 - stacking photoresist on the plasma-treated oxycarbide layer and patterning the resultant structure.